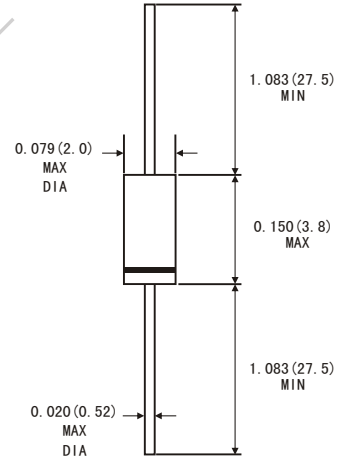


### FEATURES

- Metal-on-silicon junction
- High breakdown voltage
- Low turn-on voltage
- Ultrafast switching speed
- Primarily intended for high level UHF/VHF detection and pulse applications with broad dynamic range
- The diode is also available in the MiniMELF case with type designation LL5712.
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

### DO-35



Dimensions in inches and (millimeters)

### MECHANICAL DATA

- Case: DO-35 glass case
- Polarity: color band denotes cathode end
- Weight: Approx. 0.13 gram

### ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V <sub>RRM</sub>	20	V
Power Dissipation (infinite Heat Sink)	P <sub>tot</sub>	430	mW
Forward Continuous Current	I <sub>F</sub>	35	mA
Junction and Storage temperature range	T <sub>J</sub> /T <sub>STG</sub>	-55 to +150	°C
Maximum Lead Temperature for Soldering during 10S at 4mm from Case	T <sub>L</sub>	230	°C

### ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakover voltage at I <sub>R</sub> =10mA	V <sub>R</sub>	20			V
Leakage current at V <sub>R</sub> =15V	I <sub>R</sub>			100	nA
Forward voltage drop at I <sub>F</sub> =1mA Test pulse: t <sub>p</sub> ≤ 300ms δ < 2% I <sub>F</sub> =35mA	V <sub>F</sub>			0.55	V
	V <sub>F</sub>			1.0	V
Junction Capacitance at V <sub>R</sub> =0V, f=1MHz	C <sub>J</sub>			1.2	PF
Thermal resistance	R <sub>θJA</sub>			400	K/W

# RATINGS AND CHARACTERISTICS CURVES 1N5712

Figure 1. forward current versus forward voltage at different temperatures (typical values)

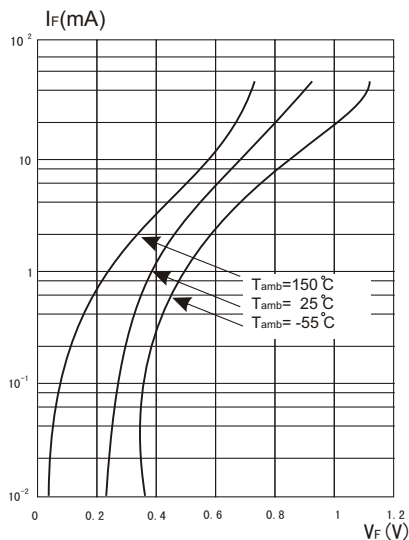


Figure 2. forward current versus forward voltage (typical values)

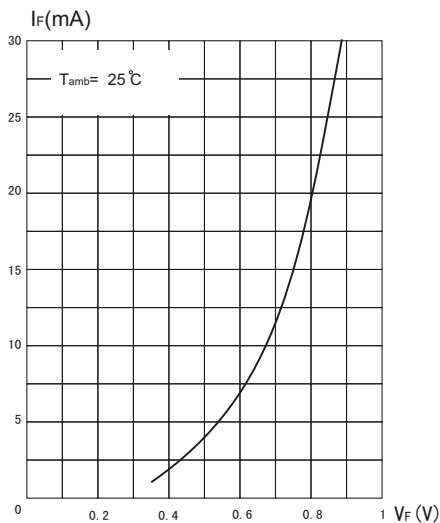
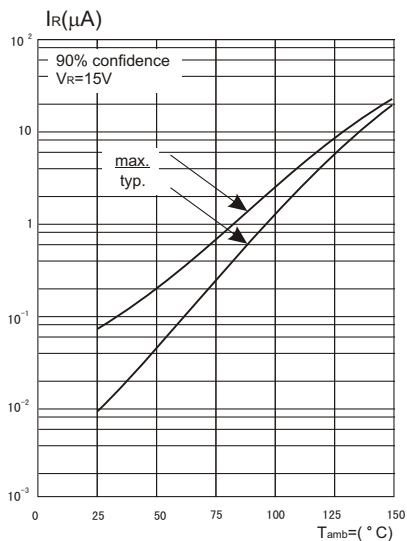


Figure 3. Reverse current versus ambient temperature



# RATINGS AND CHARACTERISTICS CURVES 1N5712

Figure 4. Reverse current versus continuous Reverse voltage (typical values)

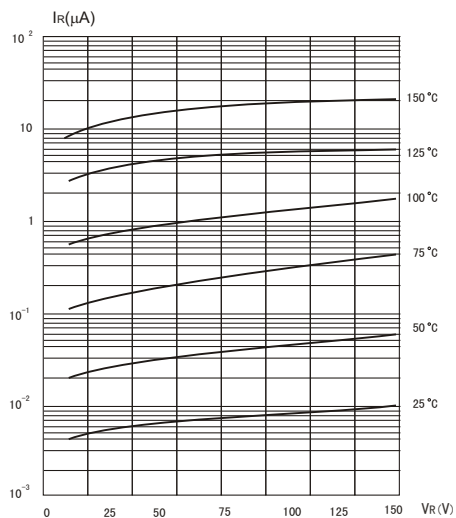


Figure 5. Capacitance C versus reverse applied voltage  $V_R$  (typical values)

